

IN THE CLAIMS

1 (Previously Presented). A method comprising:
aging an unthickened silica slurry for at least fifty days from its manufacture date;
and
using the aged, unthickened slurry to reduce defects when chemical mechanical polishing a tantalum containing layer.

2 (Original). The method of claim 1 including using chemical mechanical polishing with an aged slurry to form copper metal lines.

3 (Original). The method of claim 1 including polishing through a copper layer and a copper seed layer down to a tantalum containing layer.

4 (Original). The method of claim 3 including polishing through the tantalum containing layer down to a dielectric.

5 (Original). The method of claim 1 including using aged silica slurries to reduce defects when polishing a tantalum containing layer.

Claims 6-10 (Canceled).

11 (Previously Presented). A method comprising:
aging an unthickened silica slurry for at least fifty days from its data of manufacture; and
using the aged, unthickened slurry to reduce defects when chemical mechanical polishing a metal layer.

12 (Original). The method of claim 11 including using the slurry to polish a barrier layer.

13 (Original). The method of claim 12 including using the slurry to polish a tantalum containing layer.

14 (Original). The method of claim 11 including using chemical mechanical polishing with an aged slurry to form copper metal lines.

15 (Original). The method of claim 11 including polishing through a copper layer and a copper seed layer down to a tantalum containing layer.

Claims 16-20 (Canceled).